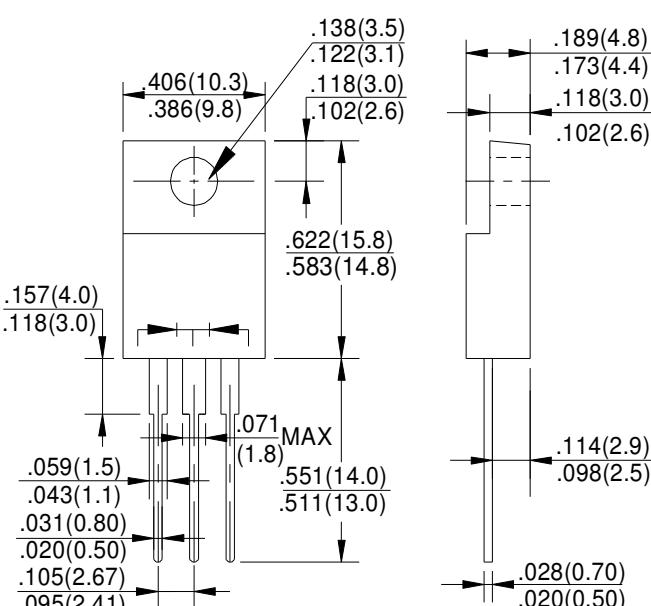


SCHOTTKY BARRIER RECTIFIERS	REVERSE VOLTAGE - 30 to 150Volts FORWARD CURRENT - 10.0 Amperes												
<b>FEATURES</b>	<b>ITO-220AB</b>												
<ul style="list-style-type: none"> <li>● Metal of silicon rectifier , majority carrier conduction</li> <li>● Guard ring for transient protection</li> <li>● Low power loss,high efficiency</li> <li>● High current capability,low VF</li> <li>● High surge capacity</li> <li>● Plastic package has UL flammability classification 94V-0</li> <li>● For use in low voltage,high frequency inverters,free wheeling, and polarity protection applications</li> </ul>	 <p>The drawing shows two views of the ITO-220AB package. The left view is a top-down cross-section with dimensions: top width 406(10.3), top height 386(9.8), guard ring height .157(4.0), guard ring thickness .118(3.0), cathode lead height .059(1.5), cathode lead thickness .043(1.1), cathode lead length .031(0.80), cathode lead thickness at base .020(0.50), cathode lead height from base .105(2.67), cathode lead thickness from base .095(2.41), total cathode lead height .551(14.0) MAX(.511(13.0)), diode lead height .138(3.5), diode lead thickness .122(3.1), diode lead height from cathode .118(3.0), diode lead thickness from cathode .102(2.6), and total diode lead height .622(15.8). The right view is a side profile with dimensions: height .583(14.8), lead thickness .189(4.8), lead height .173(4.4), lead thickness .118(3.0), lead height from cathode .102(2.6), lead thickness from cathode .114(2.9), lead height from diode .098(2.5), and lead thickness from diode .028(0.70).</p> <p>Dimensions in inches and (millimeters)</p>												
<b>MECHANICAL DATA</b>													
<ul style="list-style-type: none"> <li>● Case: ITO-220AB molded plastic</li> <li>● Polarity: As marked on the body</li> <li>● Weight: 0.08ounces,2.24 grams</li> <li>● Mounting position :Any</li> </ul>													
<b>MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS</b>													
Rating at 25°C ambient temperature unless otherwise specified. Single phase, half wave ,60Hz, resistive or inductive load. For capacitive load, derate current by 20%													
CHARACTERISTICS	SYMBOL	SRF 1030CT	SRF 1040CT	SRF 1050CT	SRF 1060CT	SRF 1080CT	SRF 10100CT	SRF 10150CT	UNIT				
Maximum Recurrent Peak Reverse Voltage	V <sub>RRM</sub>	30	40	50	60	80	100	150	V				
Maximum RMS Voltage	V <sub>RMS</sub>	21	28	35	42	56	70	105	V				
Maximum DC Blocking Voltage	V <sub>DC</sub>	30	40	50	60	80	100	150	V				
Maximum Average Forward Rectified Current ( See Fig.1) @T <sub>c</sub> =95 °C	I <sub>(AV)</sub>	10.0						A					
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Super Imposed on Rated Load (JEDEC Method)	I <sub>FSM</sub>	120						A					
Peak Forward Voltage at 5.0A DC (Note1)	V <sub>F</sub>	0.55		0.70		0.85		0.95					
Maximum DC Reverse Current @T <sub>J</sub> =25°C at Rated DC Bolcking Voltage @T <sub>J</sub> =100°C	I <sub>R</sub>	1.0 50						mA					
Typical Junction Capacitance (Note2)	C <sub>J</sub>	250						pF					
Typical Thermal Resistance (Note3)	R <sub>θJC</sub>	3.0						°C/W					
Operating Temperature Range	T <sub>J</sub>	-55 to +150						°C					
Storage Temperature Range	T <sub>STG</sub>	-55 to +150						°C					
NOTES: 1.300us pulse width,2% duty cycle. 2.Measured at 1.0 MHz and applied reverse voltage of 4.0V DC. 3.Thermal resistance junction to case.													
REV. 1, 30-Dec-2011													

# RATING AND CHARACTERISTIC CURVES

## SRF1030CT thru SRF10150CT

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FIG. 1 – FORWARD CURRENT DERATING CURVE

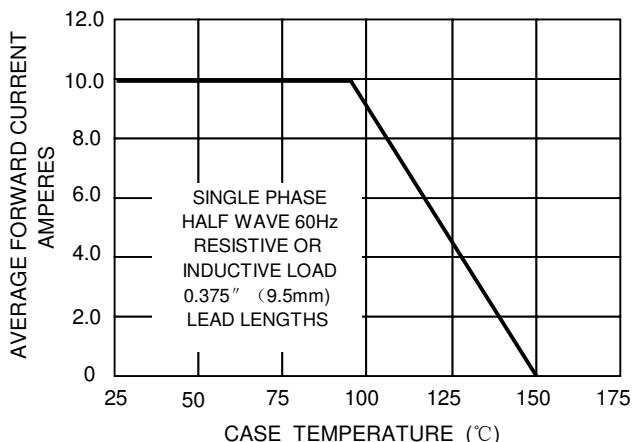


FIG. 2 – MAXIMUM NON-REPETITIVE SURGE CURRENT

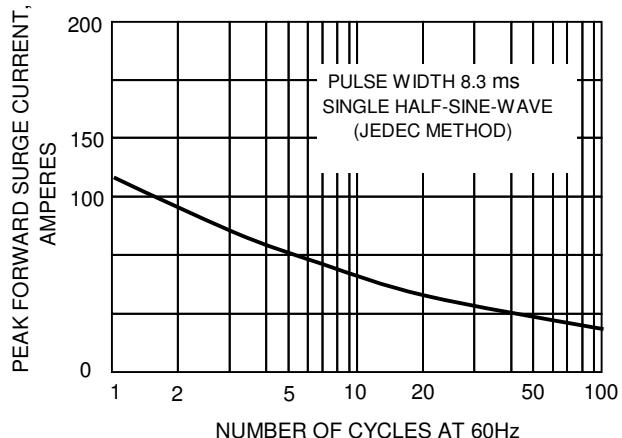


FIG.3-TYPICAL REVER CHARACTERISTICS

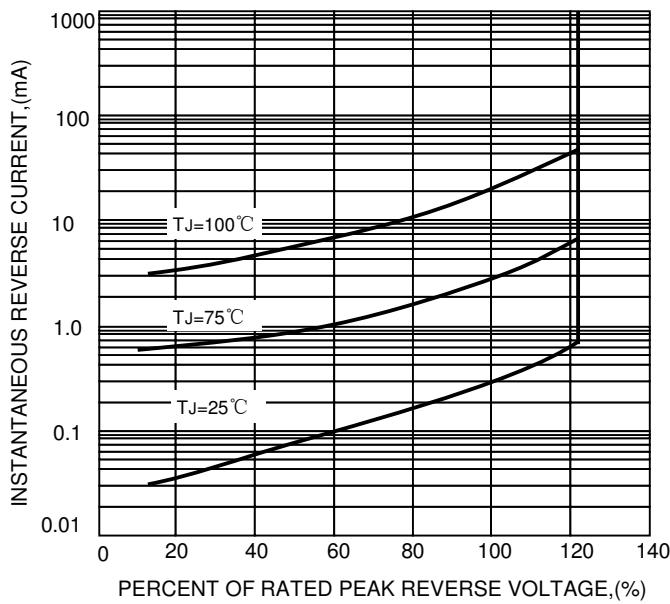


FIG.4-TYPICAL FORWARD CHARACTERISTICS

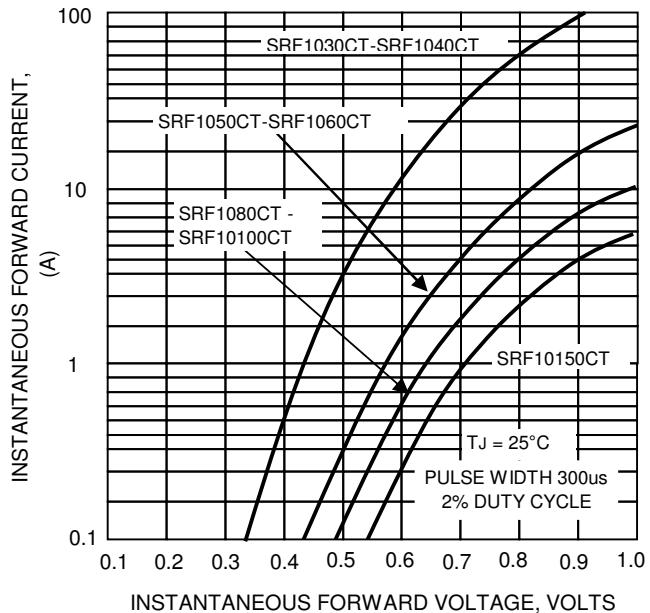


FIG.5 – TYPICAL JUNCTION CAPACITANCE

